Ceramic, Hermetic

SPDT RF Switch

50Ω 500-6000 MHz

Absorptive RF Switch with internal driver. Single Supply Voltage, +3V to +5V

Product Features

- Wide bandwidth, 500 to 6000 MHz
- High Isolation, 65 dB typ. at 1 GHz
- Low insertion loss, 1.0 dB typ.
- Internal CMOS driver
- Fast switching, Rise/fall time, 30 ns typ.
- Built rugged for tough environments
- Hermetically sealed
- Wide operating temperature, -55°C to 125°C

Typical Applications

- Automated switching networks
- Cellular
- PCN
- ISM, WCDMA, WiMAX
- Military



CSWA2-63DR+

CASE STYLE: DG1293 PRICE: \$4.95 ea. QTY. (10-49)

MIL screening available
Please consult Applications Dept.

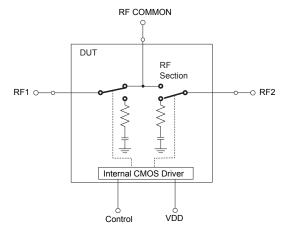
+ RoHS compliant in accordance with EU Directive (2002/95/EC)

The +Suffix has been added in order to identify RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications.

General Description

The CSWA2-63DR+ is a 50Ω high isolation, absorptive SPDT RF switch designed for wireless applications, covering a broad frequency range from 500 to 6000 MHz with low insertion loss. In non absorptive mode, the switch is usable down to 0.3 MHz. It may also be used in 75Ω systems over 0.3-3000 MHz. The CSWA2-63DR+ operates on a single supply voltage in the range of +3V to +5V. This unit includes an internal CMOS driver. The switch consumes very low supply current, 18 μ A typ. The CSWA2-63DR+ switch comes in a low profile hermetic very small size package, 4mm x 4mm x 1.2mm. Expected MTBF is 373 years at 85°C case temperature.

Schematic and Application Circuit



Cblock should be free of resonance over frequency of operation.

Frequency (MHz)	Cblock (Suggested value)
0.3-500	0.1µF
500-6000	47pF

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For detailed performance specs & shopping online see web site

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Notes: 1. Performance and quality attributes and conditions not expressly stated in this specification sheet are intended to be excluded and do not form a part of this specification sheet. 2. Electrical specifications and performance data contained herein are based on Mini-Circuit's applicable established test performance orientein and measurement instructions. 3. The parts covered by this specification sheet are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the Standard Terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at www.minicircuits.com/WCLStore/terms.jsp.

RF Electrical Specifications⁽¹⁾, 500 - 6000 MHz, $T_{AMB}=25$ °C, $V_{DD}=+3V$ to +5V

Parameter		Min.	Тур.	Max.	Units	
Frequency Range		500		6000	MHz	
	0.3 to 500 MHz		1.0			
	500 to 2000 MHz		1.0	1.3		
Insertion Loss	2000 to 3000 MHz		1.1	1.4	dB	
	3000 to 4000 MHz		1.2	1.5	иБ	
	4000 to 6000 MHz		1.5	1.8		
	0.3 to 500 MHz		60			
	500 to 2000 MHz	54	70			
Isolation between Common port and RF1/RF2 Ports	2000 to 3000 MHz	50	60		dB	
	3000 to 4000 MHz	50	54		ив	
	4000 to 6000 MHz	40	44			
	0.3 to 500 MHz		76			
	500 to 2000 MHz	52	64			
Isolation between RF1 and RF2 ports	2000 to 3000 MHz	50	54		-ID	
·	3000 to 4000 MHz	44	50		dB	
	4000 to 6000 MHz	36	44			
	0.3 to 500 MHz		20			
	100 to 2000 MHz		20			
Deturn Less (ON STATE)	2000 to 3000 MHz		15		dB	
Return Loss (ON STATE)	3000 to 4000 MHz		15			
	4000 to 6000 MHz		15			
	500 to 2000 MHz		13			
Deturn Loss @ DE1/DE2 north (OFF STATE)	2000 to 3000 MHz		13		dB	
Return Loss @ RF1/RF2 ports (OFF STATE)	3000 to 4000 MHz		14		ив	
	4000 to 6000 MHz		14			
	V _{DD} =3V, 500 to 2000 MHz		47			
I IPO	2000 to 6000 MHz		40		dBm	
Input IP3	V _{DD} =5V, 500 to 2000 MHz		50			
	2000 to 6000 MHz		45			
	V _{pp} =3V, 500 to 2000 MHz		24			
(0)	2000 to 6000 MHz		24			
Input 1dB Compression (2)	V _{DD} =5V, 500 to 2000 MHz		30		dBm	
	2000 to 6000 MHz		27			

DC Electrical Specifications

Parameter	Min.	Тур.	Max.	Units
VDD, Supply Voltage	3		5	V
Supply Current (V _{DD} = 5V) ⁽³⁾		18		μΑ
Control Voltage Low	0		0.5	V
Control Voltage High ⁽⁴⁾	2.7		V _{DD}	V
Control Current		5		μΑ

Notes:

Switching Specifications at V_{DD}=5V

Parameter	Min.	Тур.	Max.	Units
Rise/Fall Time (10 to 90% or 90 to 10% RF)		23		nSec
Switching Time (50% CTRL to 90/10% RF)		35		nSec
Video Feedthrough (Control 0-5V, Frequency 1 MHz)		25		mV _{P-P}



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IF/RF MICROWAVE COMPONENTS

Insertion loss values are deembedded from test board loss. Tested using Agilent's N5230A network analyzer with internal DC blocks, except for IP3 and compression.

^{2.} Note absolute maximum rating for input and dissipated power. At 5V, over 2000-6000 MHz, 0.2 dB compression.

^{3.} Increases with switching repetition rate. See graph.

^{4.} CMOS interface latch-up condition may occur when logic high signal is applied prior to power supply.

Absolute Maximum Ratings

Parameter	Ratings			
Operating Temperature	-55°C to 125°C			
Storage Temperature	-65°C to 150°C			
V _{DD} , Supply Voltage	2.7 to 5.5V			
Voltage Control	-0.2V Min. V _{DD} Max.			
RF input power	1Watt			
Dissipated Power at 25°C	370mW			
ESD, HBM	Class 1A (250 to <500V) per JESD22-A114			
ESD, MM	Class A (passes 50V) per JESD22-A115			
ESD, CDM	Class III (500 to <1000V) per JESD22-C101			

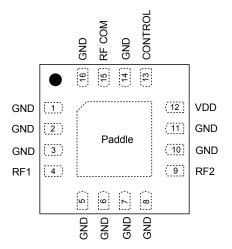
Truth Table (State of control voltage selects the desired switch state)

State of control voltage selects the desired switch state)				
State of Control Voltage	Switch State -	Switch State - RF Common to		
State of Control Voltage	RF1	RF2		
Low	ON	OFF		
High	OFF	ON		
ON- low insertion loss state OFF- Isolation State				

Pad Connections

Function	Pad Number	Description
RF COM	15	RF Common/ SUM Port
RF1	4	RF Out #1/In Port #1
RF2	9	RF Out #1/In Port #2
Control	13	CMOS Control IN
VDD	12	Supply Voltage
GND	1,2,3,5,6,7,8,10, 11,14,16, paddle	RF Ground

Pad Configuration (Top View)



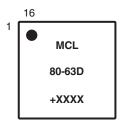
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Product Marking



Additional Detailed Technical Information

Additional information is available on our web site. To access this information enter the model number on our web site home page.

Performance data, graphs

Case Style: DG1293

Ceramic, finish: gold over nickel

Tape & Reel: F70

Suggested Layout for PCB Design: PL-279

Evaluation Board: TB-461+

Environmental Ratings: ENV40



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